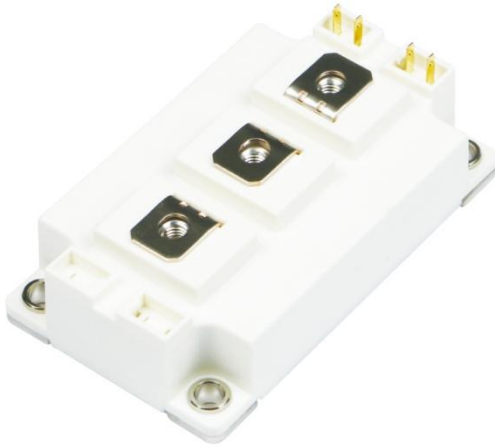


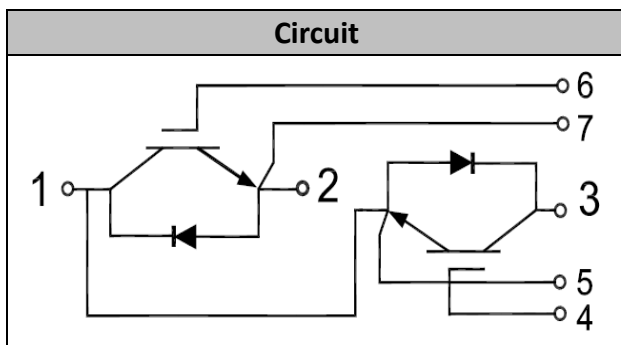


IGBT Modules

V_{CES}	1200V
I_C	150A

Applications

- High frequency drivers
- Solar inverters
- UPS (Uninterruptible Power Supplies)
- Electric welding machine



Features

- High speed IGBT in NPT technology
- Low switching losses
- High short circuit capability(10us)
- Including ultra fast & soft recovery anti-parallel FWD
- Low inductance
- Maximum junction temperature 150°C

● IGBT

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Collector-Emitter Voltage	V_{CES}	$V_{GE}=0V, I_C=1mA, T_{vj}=25^{\circ}C$	1200	V
Continuous Collector Current	I_C	$T_c=80^{\circ}C$	150	A
Repetitive Peak Collector Current	I_{CRM}	$t_p=1ms$	300	A
Gate-Emitter Voltage	V_{GES}	$T_{vj}=25^{\circ}C$	± 20	V
Total Power Dissipation	P_{tot}	$T_c=25^{\circ}C$ $T_{vjmax}=150^{\circ}C$	960	W



MG150HF12LEC2

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Characteristic Values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=6mA, T_{vj}=25^{\circ}C$	5.0	5.8	6.5	V
Collector-Emitter Cut-off Current	I_{CES}	$V_{CE}=1200V, V_{GE}=0V, T_{vj}=25^{\circ}C$			1.0	mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=150A, V_{GE}=15V, T_{vj}=25^{\circ}C$		3.4		V
		$I_C=150A, V_{GE}=15V, T_{vj}=125^{\circ}C$		3.9		
		$I_C=150A, V_{GE}=15V, T_{vj}=150^{\circ}C$		4.15		
Gate Charge	Q_G			2.86		uC
Input Capacitance	C_{ies}	$V_{CE}=25V, V_{GE}=0V,$ $f=1MHz, T_{vj}=25^{\circ}C$		9.8		nF
Reverse Transfer Capacitance	C_{res}			0.6		nF
Gate-Emitter leakage current	I_{GES}	$V_{CE}=0V, V_{GE}=20V, T_{vj}=25^{\circ}C$			400	nA
Turn-on Delay Time	$t_{d(on)}$	$I_C=150A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=4.7\Omega$ $T_{vj}=25^{\circ}C$		137		ns
Rise Time	t_r			115		ns
Turn-off Delay Time	$t_{d(off)}$			390		ns
Fall Time	t_f			33		ns
Energy Dissipation During Turn-on Time	E_{on}			23.3		mJ
Energy Dissipation During Turn-off Time	E_{off}			5.1		mJ
Turn-on Delay Time	$t_{d(on)}$	$I_C=150A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=4.7\Omega$ $T_{vj}=150^{\circ}C$		133		ns
Rise Time	t_r			106		ns
Turn-off Delay Time	$t_{d(off)}$			426		ns
Fall Time	t_f			77		ns
Energy Dissipation During Turn-on Time	E_{on}			29.5		mJ
Energy Dissipation During Turn-off Time	E_{off}			9.1		mJ
SC Data	I_{sc}	$t_p \leq 10\mu s, V_{GE}=15V, T_{vj}=150^{\circ}C,$ $V_{CC}=600V, V_{CEM} \leq 1200V$		450		A



● Diode

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	$T_{vj}=25^{\circ}\text{C}$	1200	V
Continuous DC Forward Current	I_F		150	A
Repetitive Peak Forward Current	I_{FRM}	$t_p=1\text{ms}$	300	A

Characteristic Values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Forward Voltage	V_F	$I_F=150\text{A}, T_{vj}=25^{\circ}\text{C}$		2.05	2.80	V
		$I_F=150\text{A}, T_{vj}=125^{\circ}\text{C}$		1.90		
		$I_F=150\text{A}, T_{vj}=150^{\circ}\text{C}$		1.80		
Recovered Charge	Q_{rr}	$I_F=150\text{A}$ $V_R=600\text{V}$ $-di_F/dt=1100\text{A/us}$ $T_{vj}=25^{\circ}\text{C}$		7.87		μC
Peak Reverse Recovery Current	I_{rr}			34		A
Reverse Recovery Energy	E_{rec}			2.44		mJ
Recovered Charge	Q_{rr}	$I_F=150\text{A}$ $V_R=600\text{V}$ $-di_F/dt=1100\text{A/us}$ $T_{vj}=150^{\circ}\text{C}$		26.16		μC
Peak Reverse Recovery Current	I_{rr}			71		A
Reverse Recovery Energy	E_{rec}			9.2		mJ

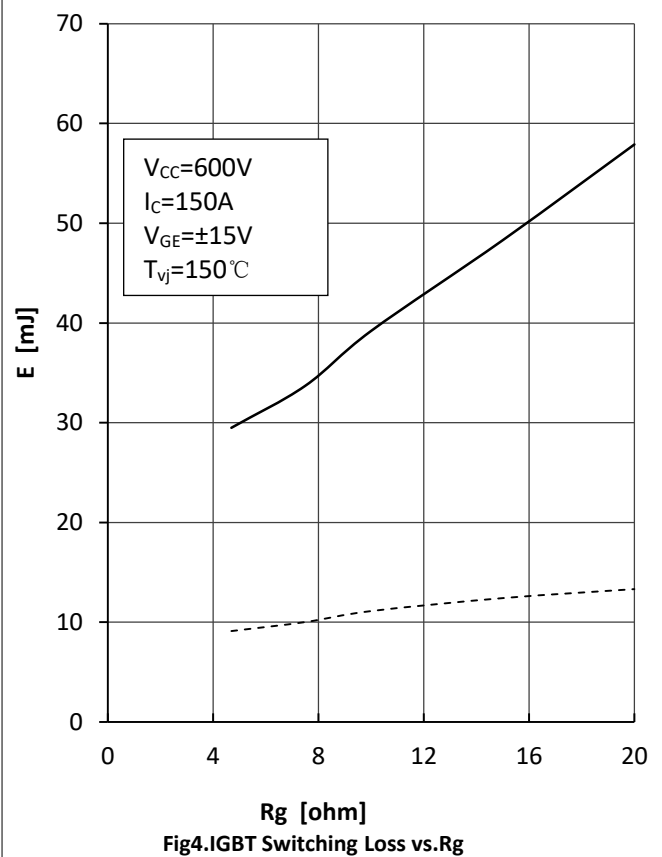
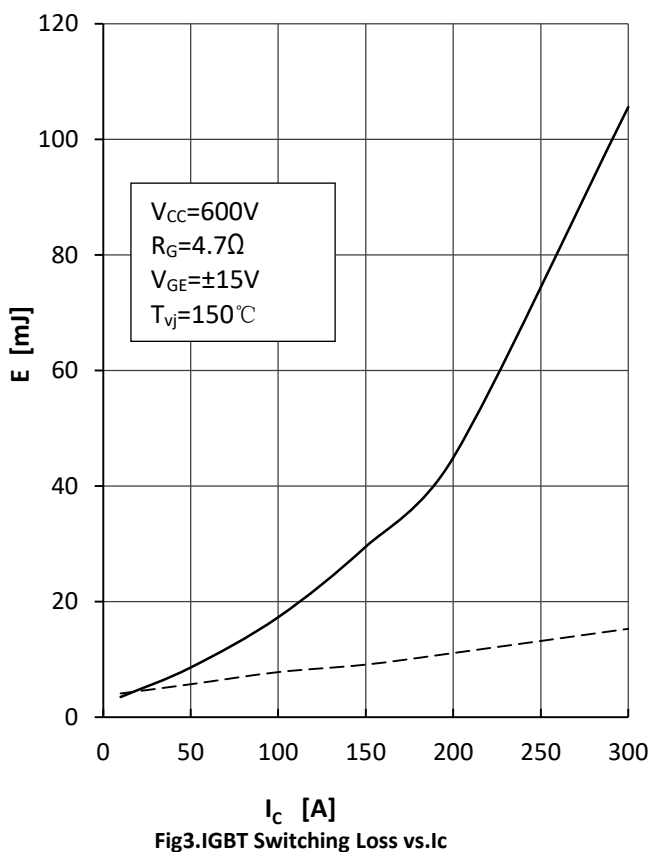
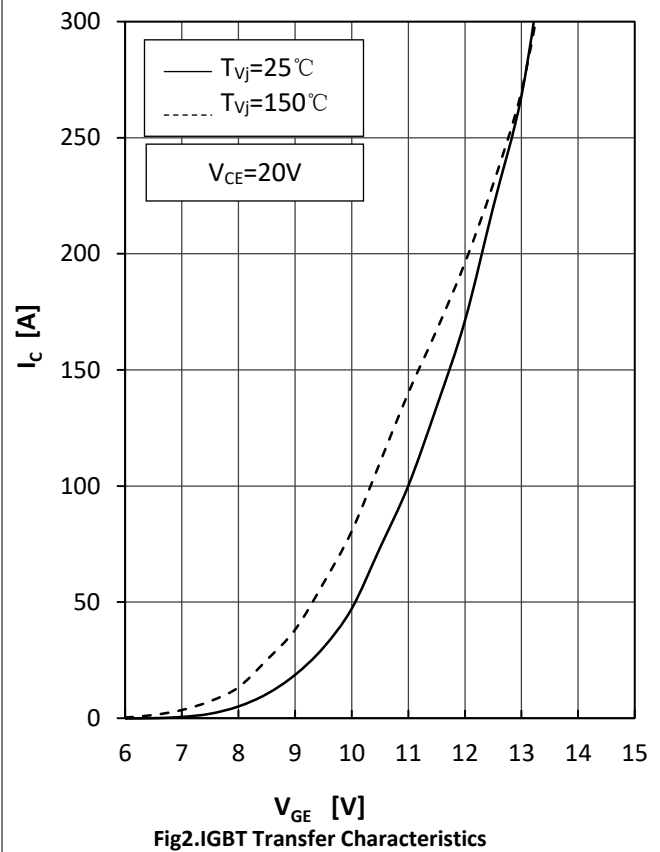
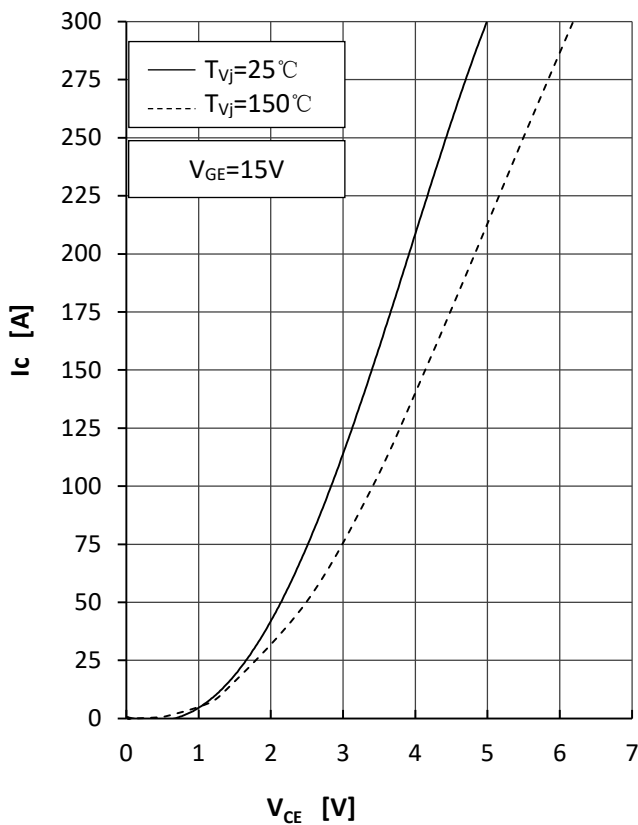


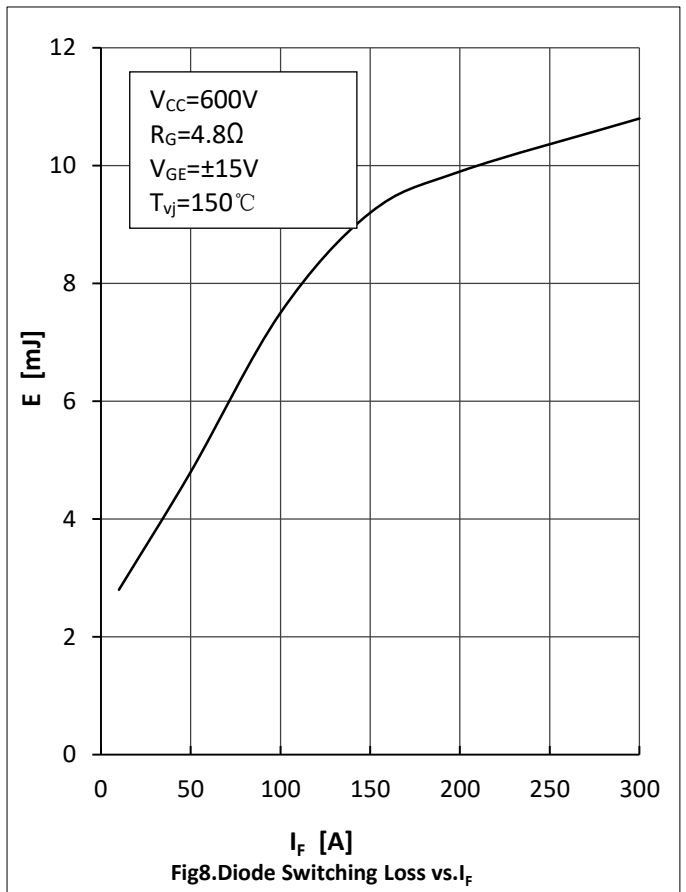
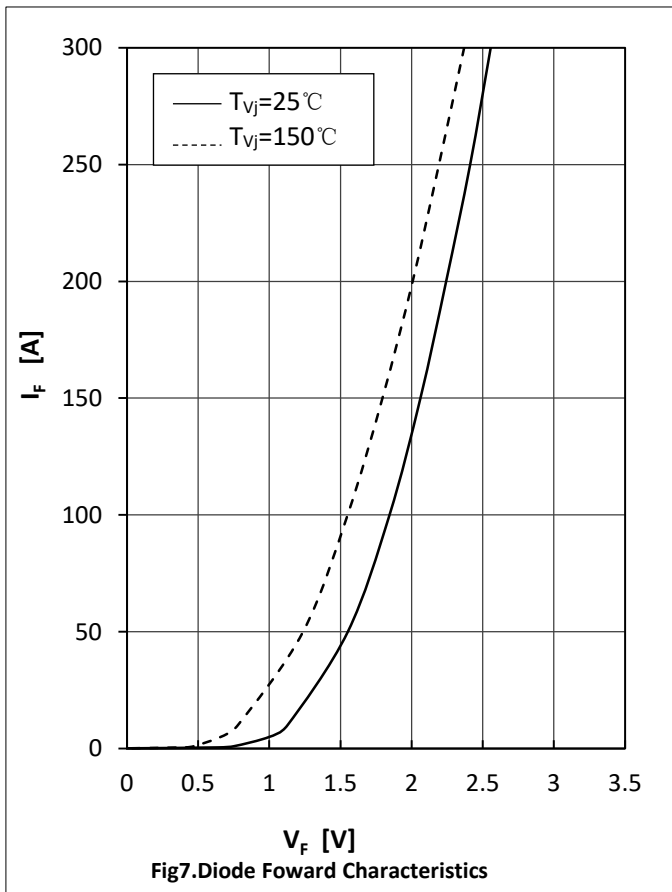
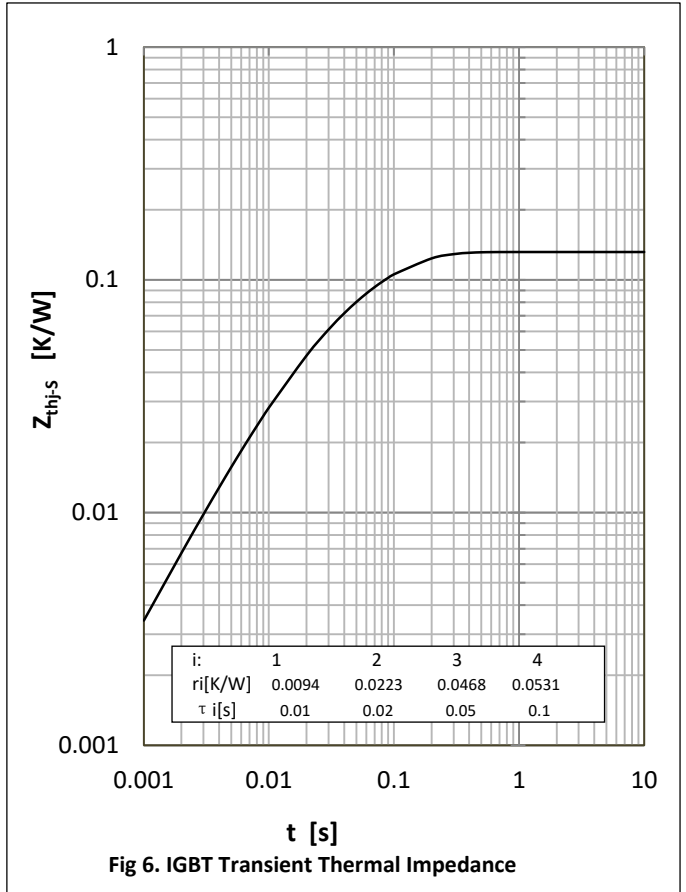
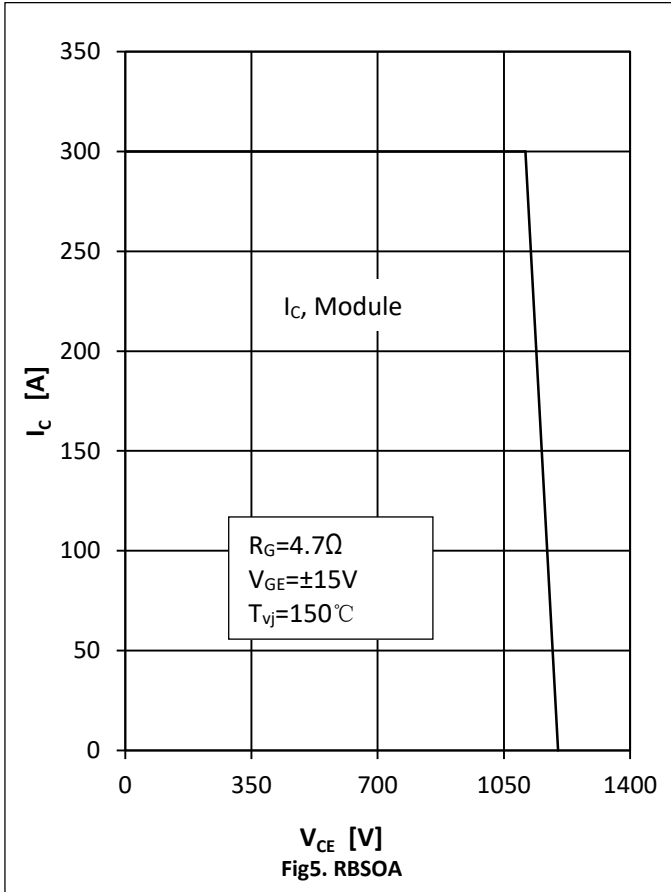
MG150HF12LEC2

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● **Module Characteristics** $T_C=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Isolation Voltage	V_{isol}	$t=1\text{min}, f=50\text{Hz}$	2500			V
Maximum Junction Temperature	T_{jmax}				150	$^{\circ}\text{C}$
Operating Junction Temperature	$T_{\text{vj op}}$		-40		125	$^{\circ}\text{C}$
Storage Temperature	T_{stg}		-40		125	$^{\circ}\text{C}$
Thermal Resistance Junction to Case	$R_{\theta\text{JC}}$	per IGBT			0.13	K/W
		per Diode			0.33	
Thermal Resistance Case to Sink	$R_{\theta\text{CS}}$	Conductive grease applied		0.012	0.035	K/W
Module Electrodes Torque	M_t	Recommended(M6)	3.0		5.0	N·m
Module-to-Sink Torque	M_s	Recommended(M6)	3.0		5.0	N·m
Weight of Module	G			315		g





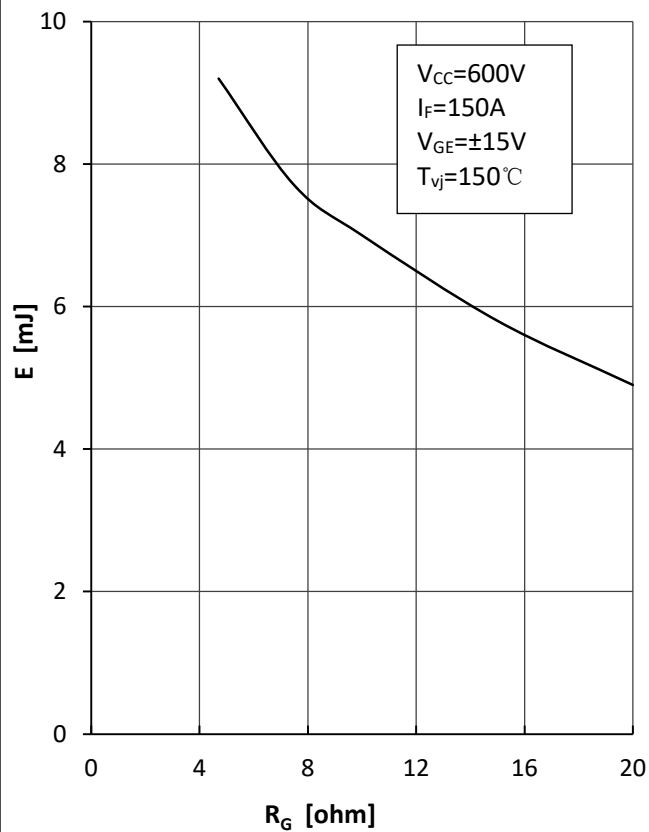


Fig9.Diode Switching Loss vs.Rg

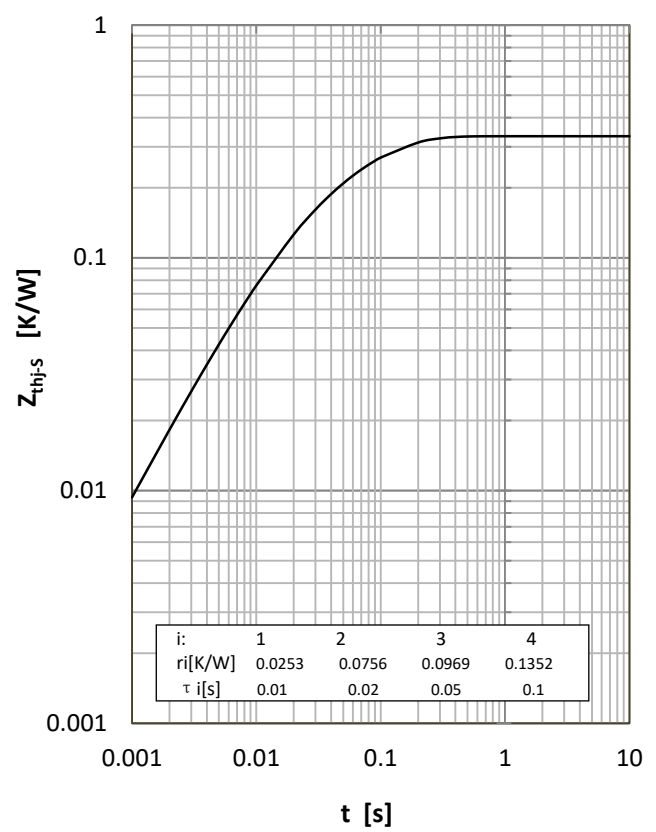
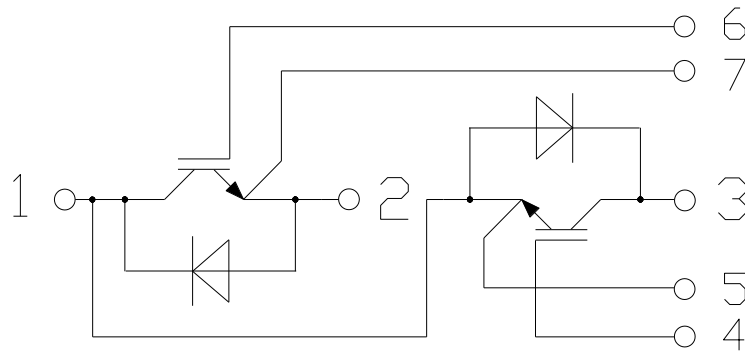


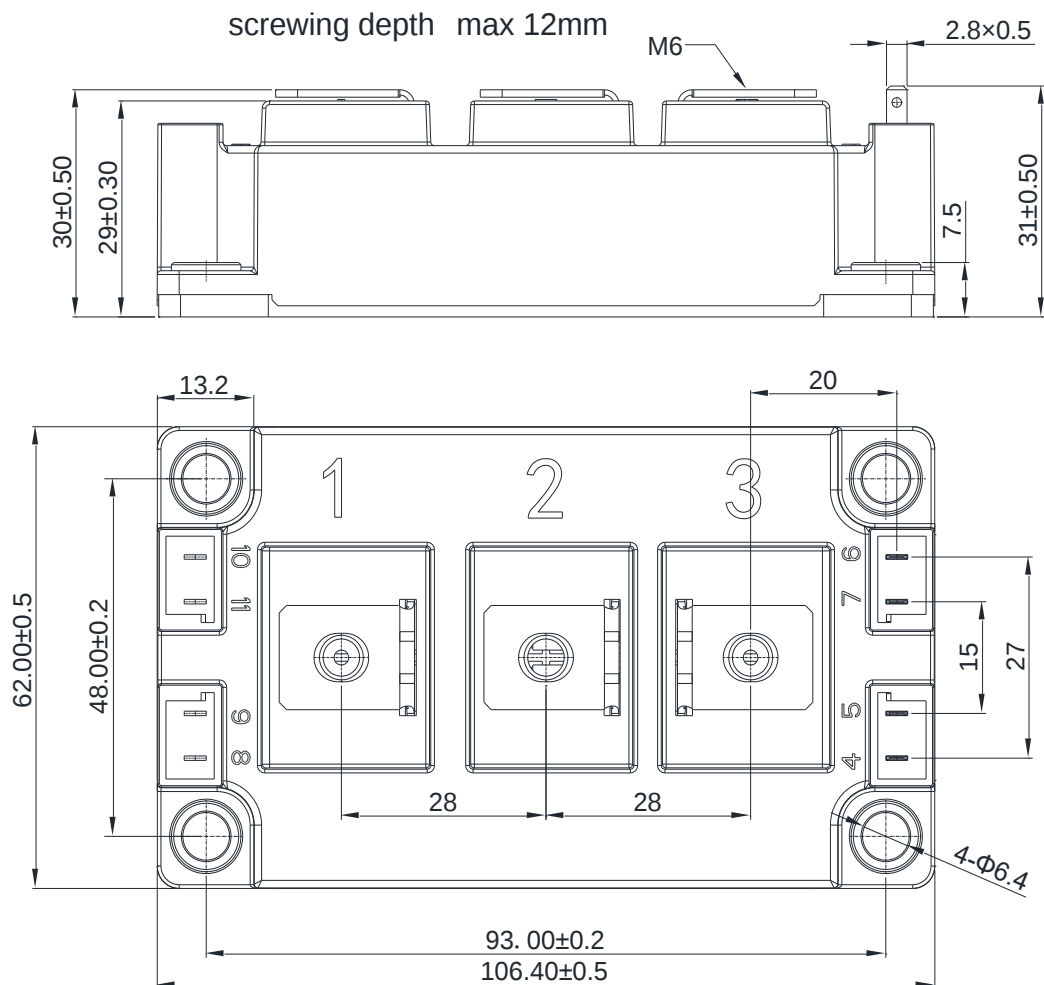
Fig10.Diode Transient Thermal Impedance

- **Circuit Diagram**



● Package Outline Information

Dimensions in Millimeters





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